

L Number	Hits	Search Text	DB	Time stamp
214	0	(tft or (thin near film near transistor)) with drain with electrode with source with gate with (semiconductor adj layer) with (aluminum or alumina) with titanium with (preventive or preventing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:39
215	0	(tft or (thin near film near transistor)) same drain same electrode same source same gate same (semiconductor adj layer) same (aluminum or alumina) same titanium same (diffusion adj (preventive or preventing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:40
216	0	(tft or (thin near film near transistor)) same drain same electrode same source same gate same (semiconductor adj layer) same (aluminum or alumina) same titanium same (diffusion adj (preventive or prevention or preventing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:41
217	719	(tft or (thin near film near transistor)).clm. and (((source adj electrode) or (drain adj electrode) and (gate adj electrode)) with aluminum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:42
218	1	(tft or (thin near film near transistor)).clm. and (((source adj electrode) or (drain adj electrode) and (gate adj electrode)) with aluminum with titanium with (diffusion adj (preventive or prevention or preventive)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:44
219	1	(tft or (thin near film near transistor)).clm. and (((source adj electrode) or (drain adj electrode) and (gate adj electrode)) with aluminum with titanium with (diffusion adj (preventive or prevention or preventive))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:45